

Ahmed

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A: I took ERSE 2610 CoCo



I took LITEC



I took CSCI-2500 Comp Org



Other



$$B1: 97_{10} = 1100001_2 = \cancel{14}_8 = 61_{10}$$

$$B2: 10110101_2 = 181_{10} = 265_8 = B5_{10}$$

$$B3: -58_{10} \rightarrow 111010 \rightarrow 000101$$

~~00111010~~

~~000101~~

~~8-bit 2's comp~~

~~1100001
+ 000101
1100011~~

$$00111010 \rightarrow 11000100$$

8-bit 2's comp. 11000110

$$B4: 01100001$$

$$+ 11000110$$

$$00100111$$

no overflow

$$B5: 58_9 \rightarrow 5 \times 9 + 8 = 53_{10}$$

$$53_{10} = 110101_2 \rightarrow 65_8$$

$$\rightarrow 35_{16}$$

C:

X \ Y	00	01	11	10
0	0	1	0	0
1	0	1	1	1

~~C ⊆ B: $\Sigma_{xyz} = \bar{x}y + yz + xz$~~

~~C ⊆ C: $\prod_{xyz} = (x+y)(\bar{x}+z)$~~

~~C ⊆ D:~~

$$C \not\subseteq B: \Sigma_{xyz} = \bar{x}y\bar{z} + \bar{x}yz + xyz + x\bar{y}z$$

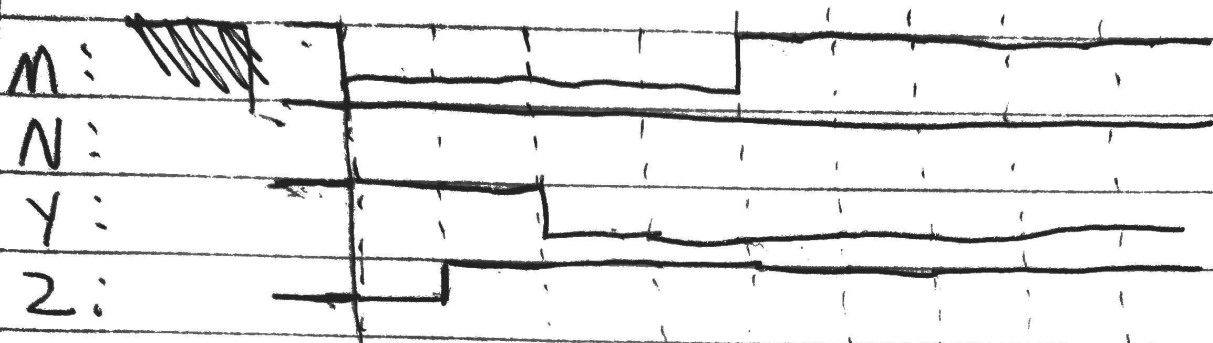
$$C \not\subseteq C: \prod_{xyz} = (x+y+z)(\bar{x}+\bar{y}+z)(\bar{x}+y+z)(x+\bar{y}+\bar{z})$$

$$C \not\subseteq D: \bar{x}y + yz + xz = \Sigma_{xyz}$$

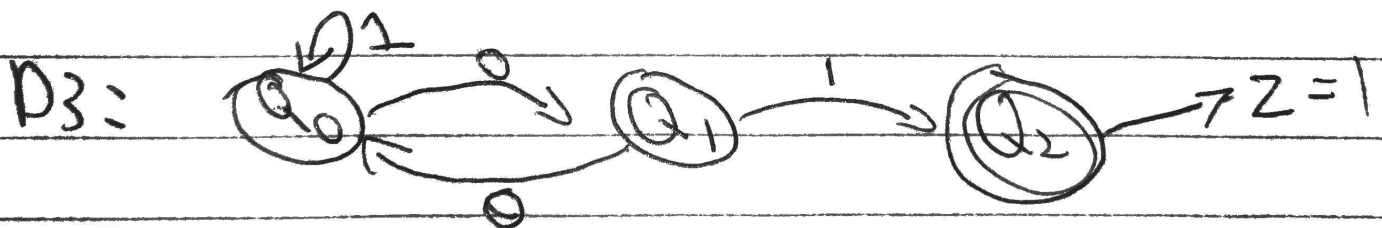
$$\begin{aligned} C \setminus B_{cont}: \bar{x}y + yz + xz &= \bar{x}y(z+\bar{z}) + yz(x+\bar{x}) + xz(y+\bar{y}) \\ &= \bar{x}yz + \bar{x}y\bar{z} + xyz + x\bar{y}z \end{aligned}$$

$$\begin{aligned} C \setminus C_{cont}: (x+y)z\bar{z}(\bar{x}+z)y\bar{y} \\ = (x+y+z)(x+\bar{y}+\bar{z})(\bar{x}+y+z)(\bar{x}+\bar{y}+\bar{z}) \end{aligned}$$

D2:



D2: SRAM and DRAM are forms of IC RAM. RAM is a form of memory that is volatile. It is fast and can be scaled fairly large. DRAM is made of capacitors and transistors and SRAM is made of latches and transistors. Thus SRAM is faster but doesn't scale as well as DRAM.



P4: The output is ready at $t = 3 \text{ ns}$